MC74HC244A

Octal 3-State Noninverting Buffer/Line Driver/ Line Receiver

High−Performance Silicon−Gate CMOS

The MC74HC244A is identical in pinout to the LS244. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This octal noninverting buffer/line driver/line receiver is designed to be used with 3−state memory address drivers, clock drivers, and other bus−oriented systems. The device has noninverting outputs and two active−low output enables.

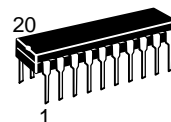The HC244A is similar in function to the HC240A.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 136 FETs or 34 Equivalent Gates
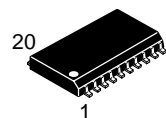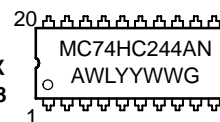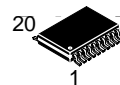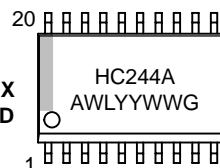- Pb−Free Packages are Available*

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http://onsemi.com

MARKING DIAGRAMS

PDIP−20
N SUFFIX
CASE 738

MC74HC244AN
AWLYYWWG

SOIC−20
DW SUFFIX
CASE 751D

HC244A
AWLYYWWG

TSSOP−20
DT SUFFIX
CASE 948E

HC
244A
ALYW▪
▪
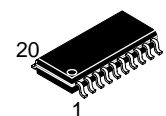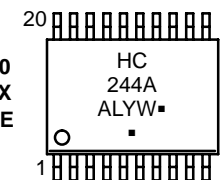
SOEIAJ−20
F SUFFIX
CASE 967

74HC244A
AWLYWWG
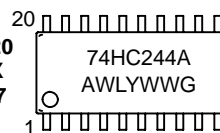
A	= Assembly Location
WL, L	= Wafer Lot
YY, Y	= Year
WW, W	= Work Week
G	= Pb−Free Package
▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

1

MC74HC244A

PIN ASSIGNMENT

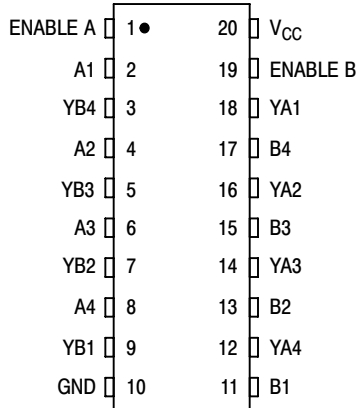|			
ENABLE A	1●	20	V_CC
A1	2	19	ENABLE B
YB4	3	18	YA1
A2	4	17	B4
YB3	5	16	YA2
A3	6	15	B3
YB2	7	14	YA3
A4	8	13	B2
YB1	9	12	YA4
GND	10	11	B1

LOGIC DIAGRAM

DATA INPUTS

A1 2 — 18 YA1
A2 4 — 16 YA2
A3 6 — 14 YA3
A4 8 — 12 YA4

B1 11 — 9 YB1
B2 13 — 7 YB2
B3 15 — 5 YB3
B4 17 — 3 YB4

NONINVERTING OUTPUTS

OUTPUT ENABLES
ENABLE A 1
ENABLE B 19

PIN 20 = V_CC
PIN 10 = GND

FUNCTION TABLE

Inputs		Outputs
Enable A, Enable B	A, B	YA, YB
L	L	L
L	H	H
H	X	Z

Z = high impedance
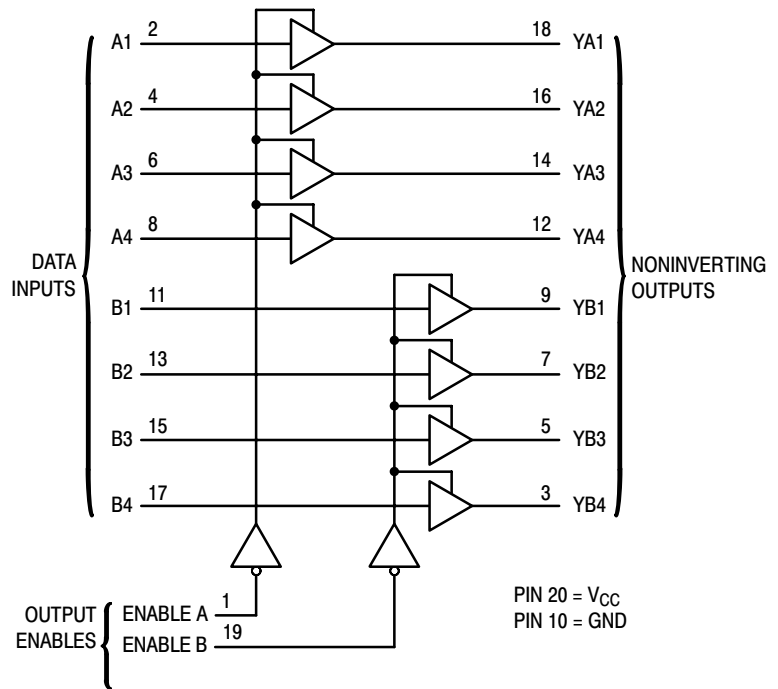
ORDERING INFORMATION

Device	Package	Shipping†
MC74HC244AN	PDIP−20	18 Units / Rail
MC74HC244ANG	PDIP−20 (Pb−Free)	18 Units / Rail
MC74HC244ADW	SOIC−20 WIDE	38 Units / Rail
MC74HC244ADWG	SOIC−20 WIDE (Pb−Free)	38 Units / Rail
MC74HC244ADWR2	SOIC−20 WIDE	1000 Tape & Reel
MC74HC244ADWR2G	SOIC−20 WIDE (Pb−Free)	1000 Tape & Reel
MC74HC244ADT	TSSOP−20*	75 Units / Rail
MC74HC244ADTG	TSSOP−20*	75 Units / Rail
MC74HC244ADTR2	TSSOP−20*	2500 Tape & Reel
MC74HC244ADTR2G	TSSOP−20*	2500 Tape & Reel
MC74HC244AF	SOEIAJ−20	40 Units / Rail
MC74HC244AFG	SOEIAJ−20 (Pb−Free)	40 Units / Rail
MC74HC244AFEL	SOEIAJ−20	2000 Tape & Reel
MC74HC244AFELG	SOEIAJ−20 (Pb−Free)	2000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

MC74HC244A

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	− 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	− 0.5 to V_{CC} + 0.5	V
V_{out}	DC Output Voltage (Referenced to GND)	− 0.5 to V_{CC} + 0.5	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA
P_D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T_{stg}	Storage Temperature	− 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: − 10 mW/°C from 65° to 125°C
                SOIC Package: − 7 mW/°C from 65° to 125°C
                TSSOP Package: − 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	− 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time V_{CC} = 2.0 V (Figure 1) V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit − 55 to 25°C	Guaranteed Limit ≤ 85°C	Guaranteed Limit ≤ 125°C	Unit
V_{IH}	Minimum High−Level Input Voltage	V_{out} = V_{CC} − 0.1 V $|I_{out}|$ ≤ 20 μA	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V_{IL}	Maximum Low−Level Input Voltage	V_{out} = 0.1 V $|I_{out}|$ ≤ 20 μA	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V_{OH}	Minimum High−Level Output Voltage	V_{in} = V_{IH} $|I_{out}|$ ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V

		V_{in} = V_{IH} $|I_{out}|$ ≤ 2.4 mA
		           $|I_{out}|$ ≤ 6.0 mA
		           $|I_{out}|$ ≤ 7.8 mA
			3.0
			4.5
			6.0
				2.48
				3.98
				5.48
					2.34
					3.84
					5.34
						2.2
						3.7
						5.2	

V_{OL}	Maximum Low−Level Output Voltage	V_{in} = V_{IL} $|I_{out}|$ ≤ 20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V

		V_{in} = V_{IL} $|I_{out}|$ ≤ 2.4 mA
		           $|I_{out}|$ ≤ 6.0 mA
		           $|I_{out}|$ ≤ 7.8 mA
			3.0
			4.5
			6.0
				0.26
				0.26
				0.26
					0.33
					0.33
					0.33
						0.4
						0.4
						0.4	

I_{in}	Maximum Input Leakage Current	V_{in} = V_{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				– 55 to 25°C	≤ 85°C	≤ 125°C	
I_{OZ}	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	± 0.5	± 5.0	± 10	µA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0$ µA	6.0	4.0	40	160	µA

NOTE: Information on typical parametric values and high frequency or heavy load considerations can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			– 55 to 25°C	≤ 85°C	≤ 125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	2.0 3.0 4.5 6.0	96 50 18 15	115 60 23 20	135 70 27 23	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 32 18 15	ns
C_{in}	Maximum Input Capacitance	–	10	10	10	pF
C_{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)	–	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Buffer)*	34	pF

* Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).
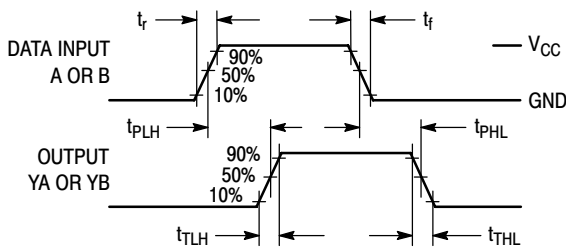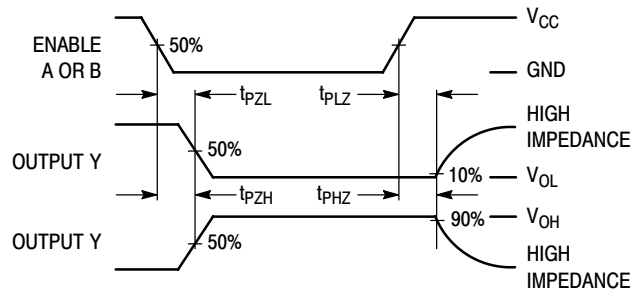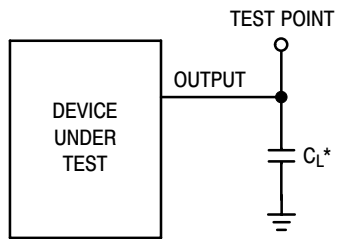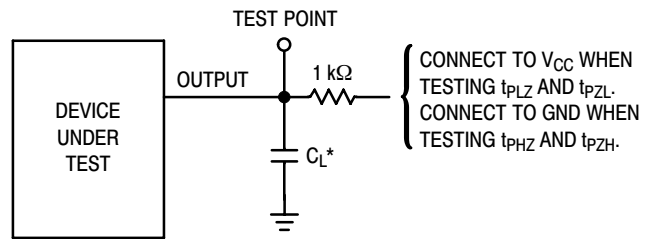
SWITCHING WAVEFORMS

Figure 1.

Figure 2.

MC74HC244A

TEST CIRCUITS

TEST POINT

OUTPUT

DEVICE UNDER TEST

C_L*

*Includes all probe and jig capacitance

Figure 3. Test Circuit

TEST POINT

OUTPUT

DEVICE UNDER TEST

1 kΩ

C_L*

CONNECT TO V_{CC} WHEN TESTING t_{PLZ} AND t_{PZL}. CONNECT TO GND WHEN TESTING t_{PHZ} AND t_{PZH}.

*Includes all probe and jig capacitance

Figure 4. Test Circuit

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, B1, B2, B3, B4
(Pins 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in noninverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROLS
Enable A, Enable B (Pins 1, 19)

Output enables (active–low). When a low level is applied to these pins, the outputs are enabled and the devices

function as noninverting buffers. When a high level is applied, the outputs assume the high impedance state.

OUTPUTS

YA1, YA2, YA3, YA4, YB1, YB2, YB3, YB4
(Pins 18, 16, 14, 12, 9, 7, 5, 3)

Device outputs. Depending upon the state of the output–enable pins, these outputs are either noninverting outputs or high–impedance outputs.

LOGIC DETAIL

TO THREE OTHER
A OR B INVERTERS

ONE OF 8 INVERTERS

DATA INPUT A OR B

V_{CC}

YA OR YB

ENABLE A OR ENABLE B
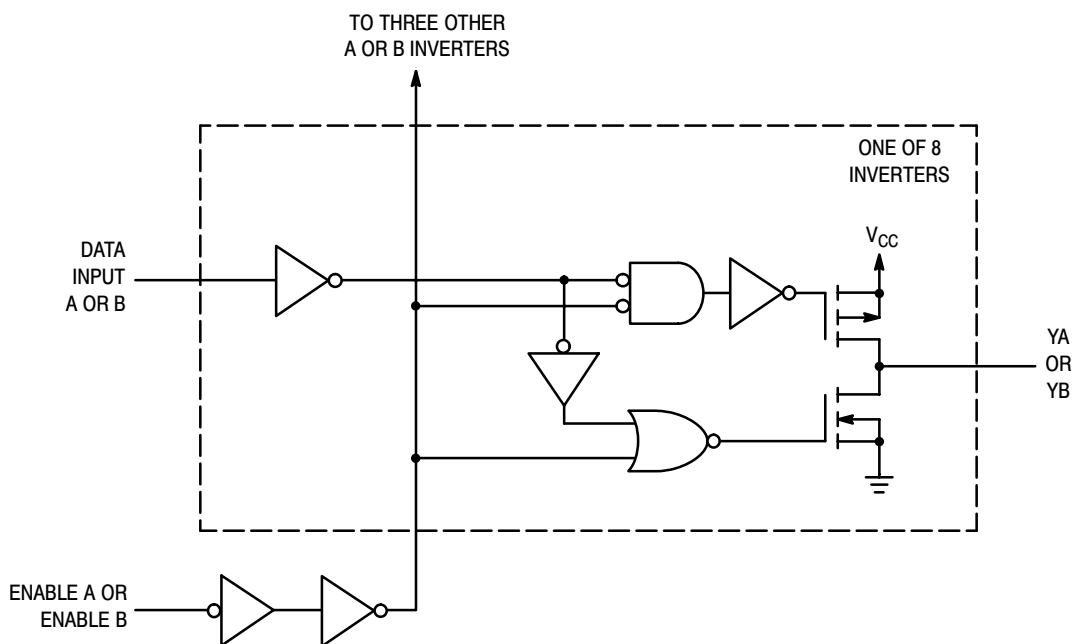
PACKAGE DIMENSIONS

PDIP–20
N SUFFIX
PLASTIC DIP PACKAGE
CASE 738–03
ISSUE E
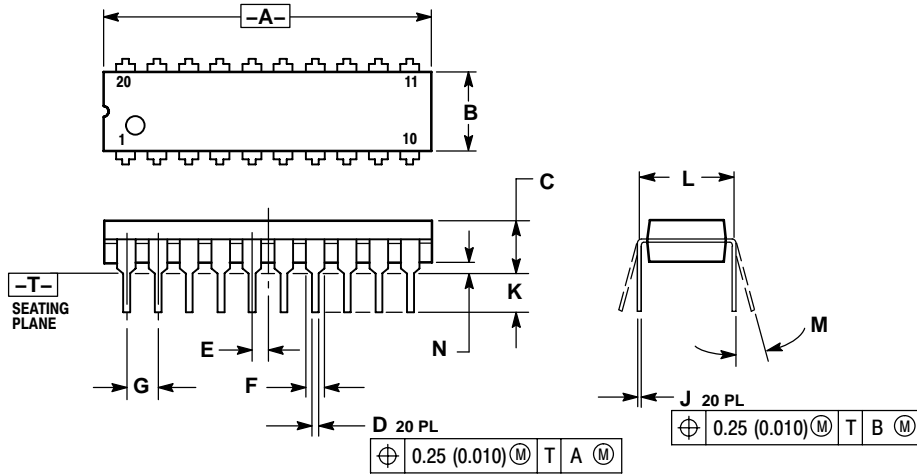
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.010	1.070	25.66	27.17
B	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

$\oplus$ | 0.25 (0.010) Ⓜ | T | A Ⓜ

$\oplus$ | 0.25 (0.010) Ⓜ | T | B Ⓜ

SOIC–20
DW SUFFIX
CASE 751D–05
ISSUE G
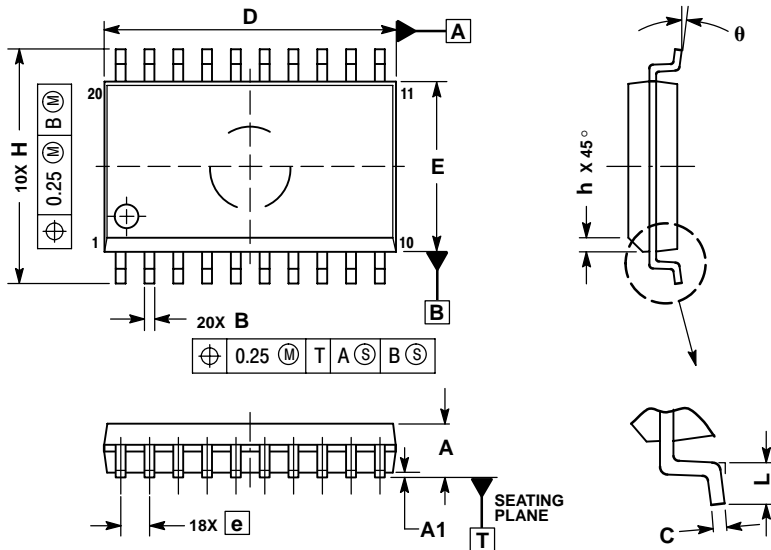
NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

$\oplus$ | 0.25 Ⓜ | T | A Ⓢ | B Ⓢ

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

MC74HC244A

PACKAGE DIMENSIONS

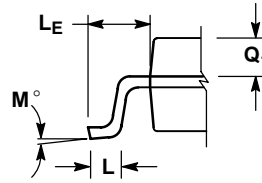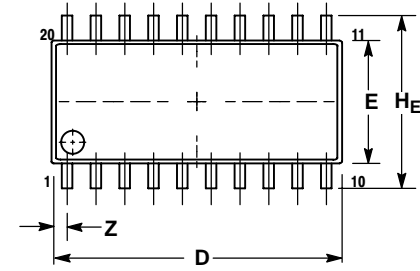**TSSOP−20**
DT SUFFIX
CASE 948E−02
ISSUE B
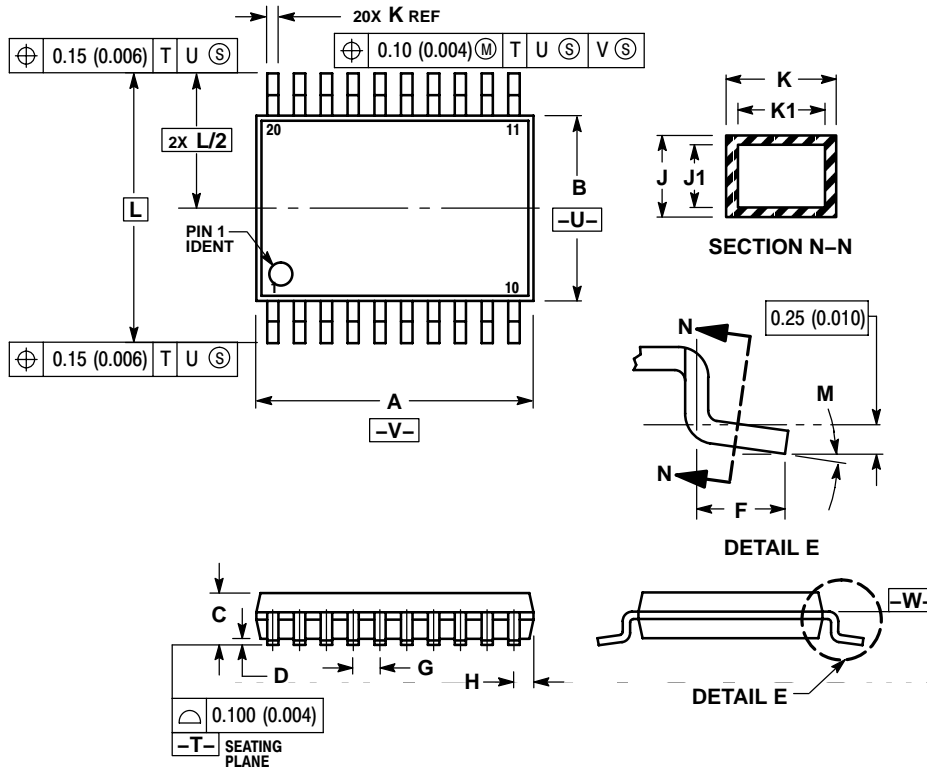
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

SECTION N−N

DETAIL E

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

MC74HC244A

PACKAGE DIMENSIONS

SOEIAJ−20
CASE 967−01
ISSUE A
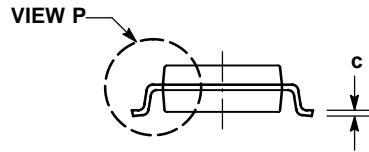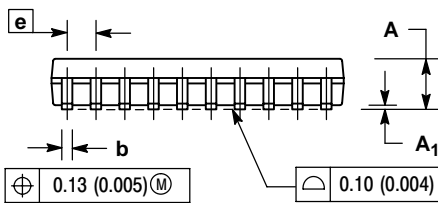
DETAIL P

VIEW P

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A$_1$	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H$_E$	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L$_E$	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q$_1$	0.70	0.90	0.028	0.035
Z	---	0.81	---	0.032